

# Searching Stable Cu<sub>x</sub>S Structures for Photovoltaic Application



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# Introduction

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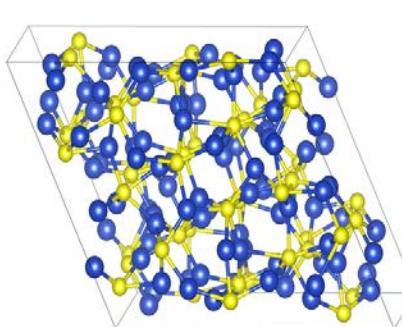
- $\text{Cu}_x\text{S}$  is one of the promising solar cell absorber materials to replace CIGS.
- Solar cells based on  $\text{Cu}_x\text{S}$  have reached an efficiency as high as 10%.
- To further improve its efficiency and especially the stability, it is important to understand the stability and electronic structure of  $\text{Cu}_x\text{S}$ .

However, due to the complexity of their crystal structures, no systematic studies have been carried out to understand the stability and electronic structure of the  $\text{Cu}_x\text{S}$  systems.

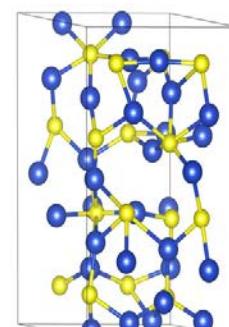
# Cu<sub>x</sub>S Crystal Structure

The experimentally identified stable compounds of Cu<sub>x</sub>S ( $1 < x \leq 2$ ):

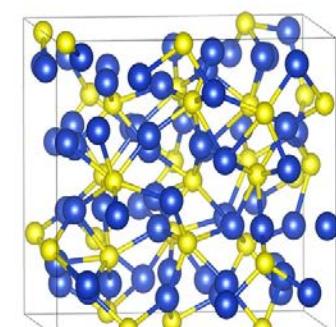
- Chalcocite (Cu<sub>2</sub>S)
- Djurleite (Cu<sub>1.94</sub>S)
- Digenite (Cu<sub>1.8</sub>S)
- Anilite (Cu<sub>1.75</sub>S)



(a) Low-Chalcocite Cu<sub>2</sub>S



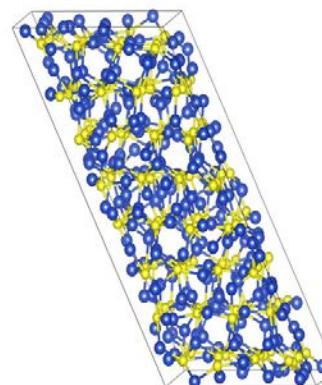
(b) High-Chalcocite Cu<sub>2</sub>S



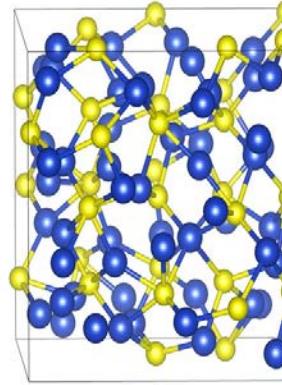
(c) Cubic-Chalcocite Cu<sub>2</sub>S

Three different structures of chalcocite Cu<sub>2</sub>S :

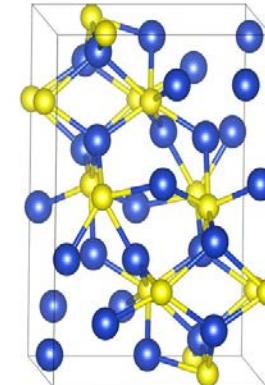
- monoclinic phase (low-chalcocite) ( $t < 104$  °C).
- hexagonal phase (high-chalcocite) ( $104$  °C  $< t < 436$  °C )
- cubic phase (cubic-chalcocite) ( $t > 436$  °C).



(d) Djurleite Cu<sub>1.94</sub>S



(e) Digenite Cu<sub>1.8</sub>S



(f) Anilite Cu<sub>1.75</sub>S

# Methods of Calculations

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- Using Vienna Ab-initio Simulation Package (VASP)
- All-electron-like projector augmented wave (PAW) potential
- The Perdew-Burke-Ernserhof (PBE) exchange correlation potential
- For more accurate calculation of band gaps, we also use hybrid functional (HSE) potentials
- Plane wave expansion up to 500eV
- The calculated cell are fully relaxed, which maximum force converges below  $0.01\text{eV}/\text{\AA}$

# The Optimized Structure Parameters and Band Gaps

The calculated lattice parameters, volume (V), band gap ( $E_g$ ), and heat of formation per formula unit ( $\Delta H$ ) of  $Cu_xS$ .

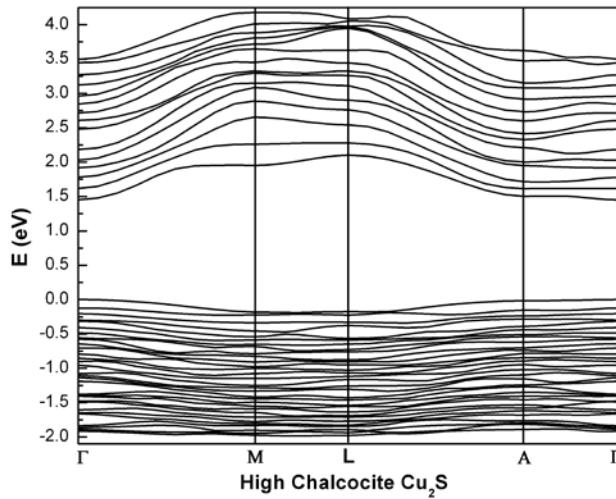
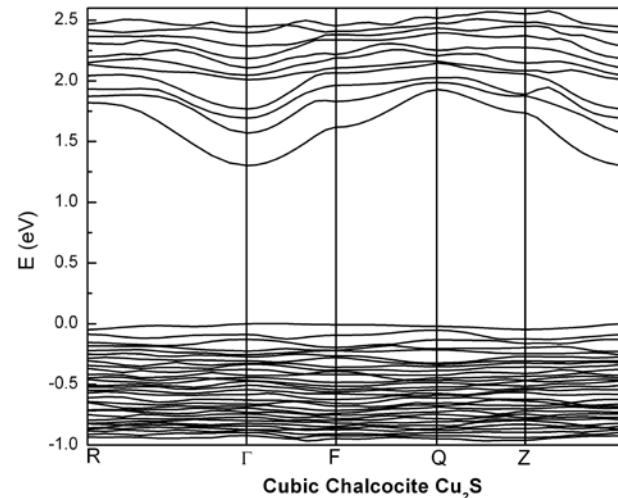
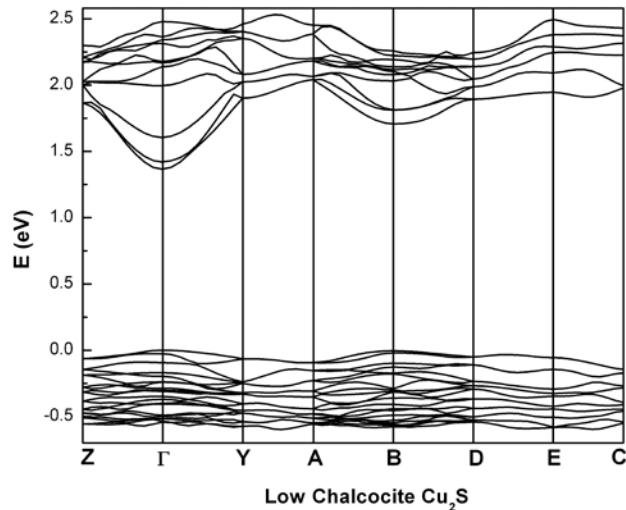
x	Crystal system	$a_0$ (Å)	$b_0$ (Å)	$c_0$ (Å)	$\alpha$	$\beta$	$\gamma$	V (Å <sup>3</sup> )	$E_g$ (eV)	$\Delta H$ (eV)
2	Monoclinic	15.27	11.93	13.45	90.0°	115.6°	90.0°	46.04	1.39	-0.40
2	Hexagonal	7.87	8.19	13.36	90.7°	90.0°	118.5°	47.28	1.49	-0.36
2	Cubic	12.04	12.26	10.47	90.3°	90.3°	87.0°	48.20	1.34	-0.34
1.94	Monoclinic	13.53	15.95	29.95	90.0°	116.7°	90.0°	45.13	1.12	-0.41
1.80	Cubic	11.36	11.15	11.27	90.6°	89.1°	91.4°	44.61	1.20	-0.38
1.75	Orthorhombic	7.91	7.98	10.92	90.0°	90.0°	90.0°	43.06	1.39	-0.44

The heat of formation  $\Delta H(x)$  of  $Cu_xS$

$$\Delta H(x) = E(Cu_xS) - xE(Cu) - E(S)$$

- Monoclinic  $Cu_2S$  is the most stable structure at  $x=2$
- Anilite  $Cu_{1.75}S$  has lowest formation energy among the calculated  $Cu_xS$  compound

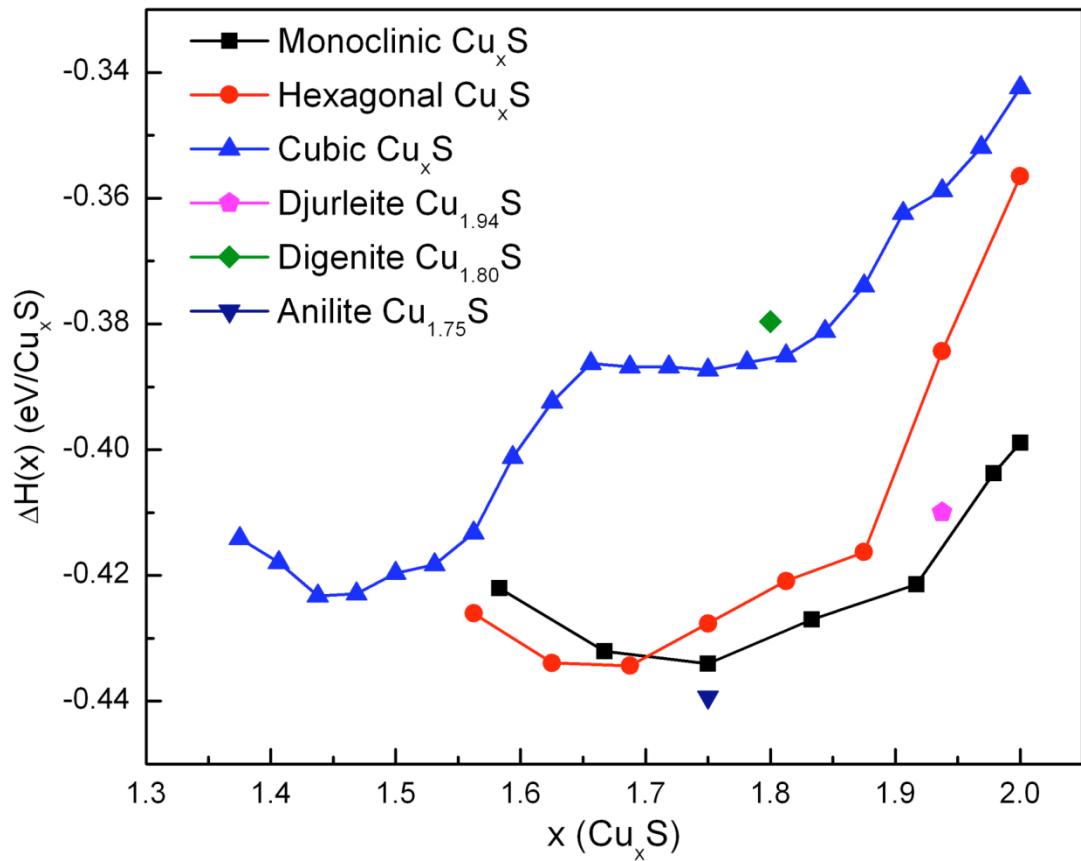
# The Band Structures of Chalcocite Cu<sub>2</sub>S



All three chalcocites have direct band gaps at  $\Gamma$  with values around 1.3–1.5 eV (HSE results).

# Calculated Heat of Formation of $\text{Cu}_x\text{S}$ as a Function of $x$

- ◆ The global minimum of the  $\Delta H(x)$  occurs at about  $x=1.7$  for the hexagonal and the monoclinic phases.
- ◆ A phase transition from the monoclinic to the hexagonal phase can occur at  $x_c \approx 1.70$ .
- ◆ However, the heat of formation of the low chalcocite and high chalcocite  $\text{Cu}_{1.75}\text{S}$  is 20meV higher than that of the anilite  $\text{Cu}_{1.75}\text{S}$ .

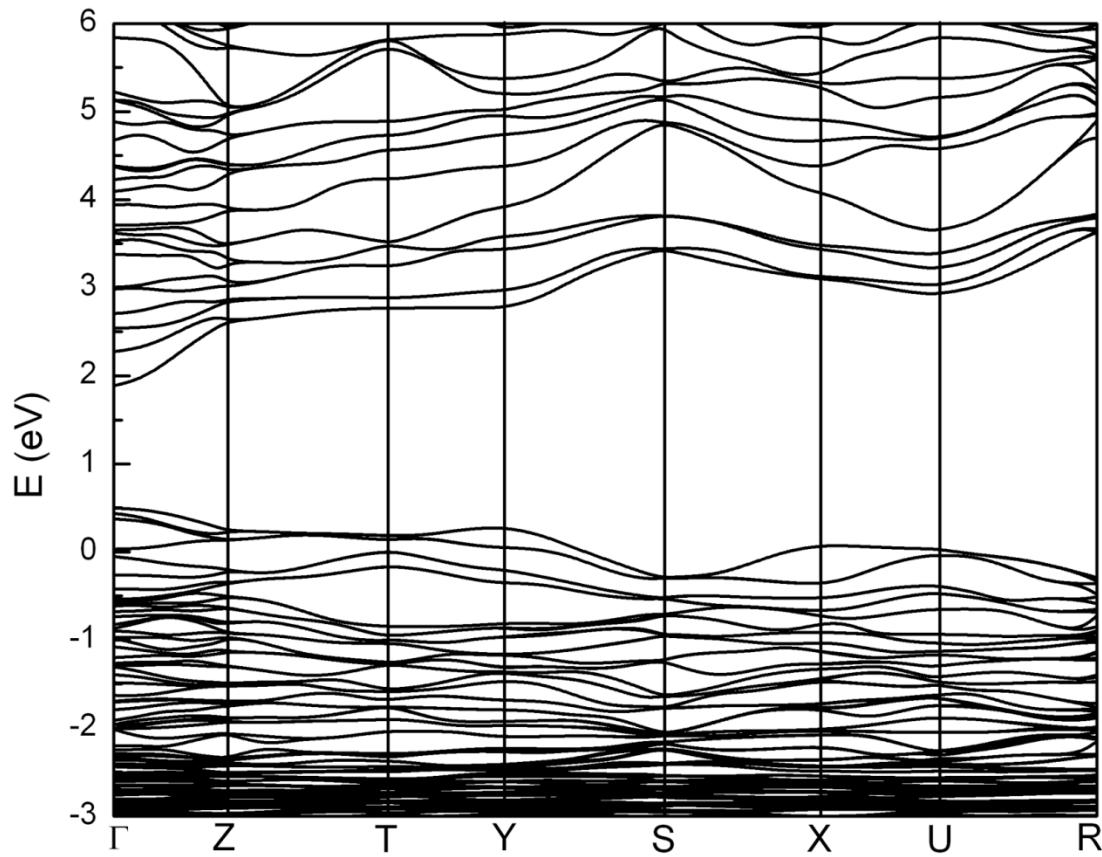


The initial structures, i.e.,  $x=2$ , are based on the three chalcocite  $\text{Cu}_2\text{S}$  structures.

The anilite structure is indeed the most stable structure among all  $\text{Cu}_x\text{S}$  at the Cu-rich limit.

# The HSE Band Structure of Anilite Cu<sub>1.75</sub>S

- ◆ It has a band gap of 1.39 eV at the  $\Gamma$  point and is heavily hole-doped
- ◆ The hole carrier concentration can be controlled by doping anilite with donors such as Sn.
- ◆ The large curvature at the band edge indicates that it should have good electron as well as hole conductivities.



We suggest that anilite based Cu<sub>x</sub>S could be promising materials for photovoltaic absorbers.

# Conclusion

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- Cu<sub>2</sub>S is more stable in the low-chalcocite structure, in agreement with experimental observations. However, it is not stable against the formation of Cu vacancies.
- We identified that at the Cu-rich limit, the most stable crystal structure is Cu<sub>1.75</sub>S in the anilite structure, which has a band gap around 1.39 eV and could be a promising solar cell absorbers.

*Thanks for Your Attention !*